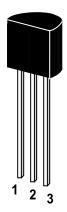
PNP Silicon Epitaxial Planar Transistor

Audio frequency low noise amplifier.

The transistor is subdivided into three group, P, F and E, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25℃)

	Symbol	Value	Unit
Collector -Base Voltage	-V _{CBO}	120	V
Collector -Emitter Voltage	-V _{CEO}	120	V
Emitter- Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	50	mA
Base Current	-I _B	10	mA
Power Dissipation	P _{tot}	300	mW
Junction Temperature	T _j	150	°С
Storage Temperature Range	Ts	-55 to +150	°С







ST 2SA1174

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at - V_{CE} =6 V , - I_{C} =1 mA					
Current Gain Group P	h _{FE}	200	-	400	-
F	h _{FE}	300	-	600	-
E	h _{FE}	400	-	800	-
at - V_{CE} =6 V , - I_{C} =0.1 mA	h _{FE}	150	500	-	-
Collector Cutoff Current					
at -V _{CB} =120V	-I _{CBO}	-	-	0.05	μΑ
Emitter Cutoff Current					
at -V _{EB} =5V	-I _{EBO}	-	-	0.05	μΑ
Collector Cutoff Current					
at -V _{CE} =100V	-I _{CEO}	-	-	1	μΑ
Gain Bandwidth Product					
at - V_{CE} =6 V , I_E =1 mA	f _T	50	100	-	MHz
Noise Voltage	NV	-	25	40	mV
Output Capacitance					
at -V _{CB} =30V, f=1MHz	C _{OB}	-	2	3	pF
Base Emitter Voltage					
at -V _{CE} =6V,-I _C =1mA	-V _{BE}	0.55	0.61	0.65	V
Collector Saturation Voltage					
at -I _C =10mA, -I _B =1mA	-V _{CE(sat)}	-	0.09	0.3	V







